

International Symposium on Combinatorial Materials Synthesis and Wide Bandgap Semiconductors

Date: January 21st and 22nd, 2019

Venue: CSB Seminar Room

Program

Date: 21-Jan-2019		Combinatorial synthesis and information integration
14:00 - 14:20		Inauguration
14:20 - 15:10	Dr. Toyohiro Chikyow NIMS, Japan	Materials screening by materials informatics and high-throughput experimentation for new materials discovery
15:10 - 16:00	Dr. Takahiro Nagata NIMS, Japan	High-throughput materials development for nano-electronic device materials
16:00 - 16:20		Tea Break
16:20 - 17:10	Dr. Yoshiyuki Yamashita, NIMS, Japan	Hard x-ray photoelectron spectroscopy for material characterization
17:10 - 17:40	Dr. P. Chinnamuthu NIT, Nagaland	Combinatorial synthesis of high-k dielectric with alternate gate channel material
19:00 -		Dinner
Date: 22-Jan-2019		Wide Bandgap Semiconductors
9:30 - 10:15	Dr. R. Muralidharan IISc, Bangalore	III- Nitride and III-Oxide semiconductors for electronic and opto-electronic applications
10:15 - 11:00	Dr. K. Jeganathan Bharathidasan Univ., Tiruchirappalli	Self-assembled In(GaN) nanowires by chemical vapor deposition
11:00 - 11:20		Tea break
11:20 - 12:05	Dr. M. Senthilkumar National Physical Lab., New Delhi	Laser molecular beam epitaxy of Group III-Nitride epilayers and nanostructures
12:05 - 12:50	Dr. K. B. Jinesh IIST, Thiruvananthapuram	Next generation memory technologies: role of wide bandgap semiconductors
12:50 - 14:00		Lunch at Central Dining Hall-1
14:00 - 16:00		Lab Tour
16:00-		Departure to Thiruvananthapuram

